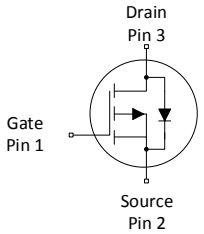
MOSFET

Small Signal MOSFET, -60 V

PG-SOT23-3

Features

- P-channel
- Very low on-resistance $R_{DS(on)}$
- Superior thermal resistance
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Logic level



Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(on),max}$	5500	mΩ
I_D	-0.29	A
Q_{oss}	-0.21	nC
Q_G	-0.29	nC

Hal Pb RoHS

Part number	Package	Marking	Related links
BSS84I	PG-SOT23-3	BI	-

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1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current [1]	I_D	-	-	-0.29	A	V_{GS}=-10 V, T_C=25 °C
				-0.19		V_{GS}=-10 V, T_C=100 °C
				-0.17		V_{GS}=-4.5 V, T_C=100 °C
				-0.18		V_{GS}=-10V, T_A=25 °C, R_{thJA}=350 °C/W [2]
Pulsed drain current [3]	$I_{D,pulse}$	-	-	-1.16	A	T_C=25 °C
Avalanche energy, single pulse [4]	E_{AS}	-	-	4	mJ	I_D=-0.18 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	0.96	W	T_C=25 °C
				0.4		T_A=25 °C, R_{thJA}=350 °C/W [2]
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

[3] See Diagram 3 for more detailed information

[4] See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	130	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}			350		

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60	-	-	V	V_{GS}=0 V, I_D=-250 µA
Gate threshold voltage	$V_{GS(th)}$	-1.0	-1.5	-2.0	V	V_{DS}=V_{GS}, I_D=-11 µA
Zero gate voltage drain current	I_{DSS}	-	-0.1	-1	µA	V_{DS}=-60 V, V_{GS}=0 V, T_j=25 °C
			-10	-100		V_{DS}=-60 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	V_{GS}=-20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	4344.4	5500	mΩ	V_{GS}=-10 V, I_D=-0.18 A
			5240.4	7000		V_{GS}=-4.5 V, I_D=-0.16 A
Gate resistance	R_G	-	45	-	Ω	-
Transconductance	g_{fs}	-	0.28	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=-0.18 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance [5)]	C_{iss}	-	18	23	pF	V_{GS}=0 V, V_{DS}=-30 V, f=1 MHz
Output capacitance [5)]	C_{oss}		3.4	4.4		
Reverse transfer capacitance [5)]	C_{rss}		1.2	2.1		
Turn-on delay time	$t_{d(on)}$	-	3.0	-	ns	V_{DD}=-30 V, V_{GS}=-10 V, I_D=-0.18 A, $R_{G,ext}$=6 Ω
Rise time	t_r		3.1			
Turn-off delay time	$t_{d(off)}$		6.8			
Fall time	t_f		48.7			

5) Defined by design. Not subject to production test.

Table 6 Gate charge characteristics [6)]

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	-0.06	-	nC	V_{DD}=-30 V, I_D=-0.18 A, V_{GS} =0 to -4.5 V
Gate charge at threshold	$Q_{g(th)}$		-0.03	-	nC	
Gate to drain charge [7)]	Q_{gd}		-0.17	-0.26	nC	
Switching charge	Q_{sw}		-0.21	-	nC	
Gate charge total [7)]	Q_g		-0.29	-0.36	nC	
Gate plateau voltage	$V_{plateau}$		-3.5	-	V	
Gate charge total [7)]	Q_g	-	-0.59	-0.78	nC	V_{DD}=-30 V, I_D=-0.18 A, V_{GS}=0 to -10 V
Output charge [7)]	Q_{oss}	-	-0.21	-0.28	nC	V_{DS}=-30 V, V_{GS}=0 V

6) See "Gate charge waveforms" for parameter definition

7) Defined by design. Not subject to production test.

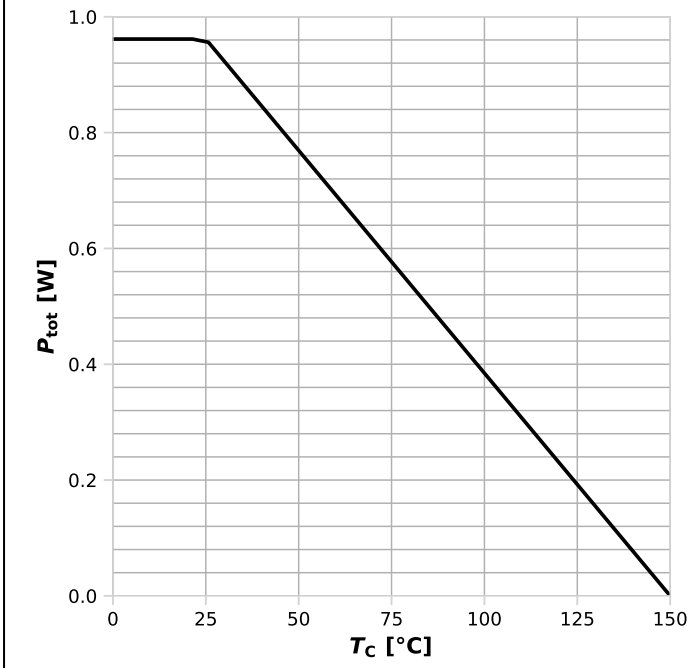
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-0.29	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$			-1.16		
Diode forward voltage	V_{SD}	-	-0.86	-1.2	V	V_{GS}=0 V, I_F=-0.18 A, T_j=25 °C
Reverse recovery time [8)]	t_{rr}	-	10.5	21.0	ns	V_R=-30 V, I_F=-0.18 A, di_F/dt=-100 A /µs
Reverse recovery charge [8)]	Q_{rr}		4.5	9.0	nC	

8) Defined by design. Not subject to production test.

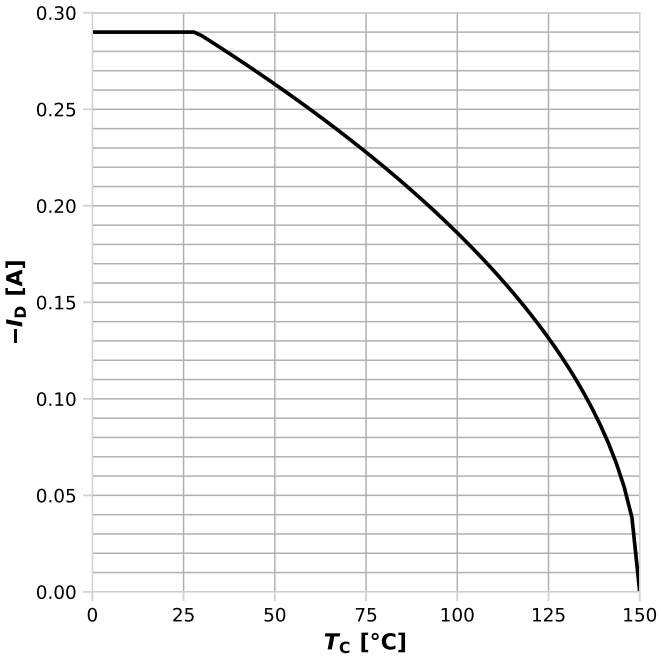
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



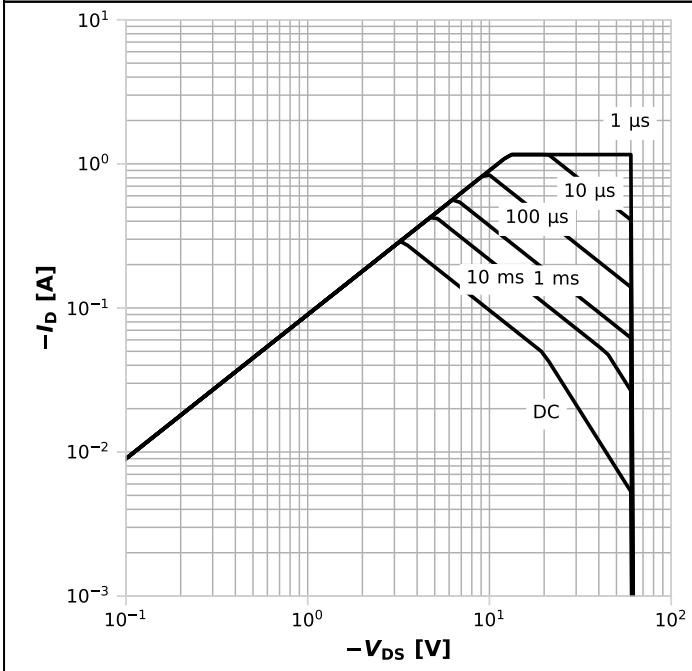
P_{tot}=f(T_C)

Diagram 2: Drain current



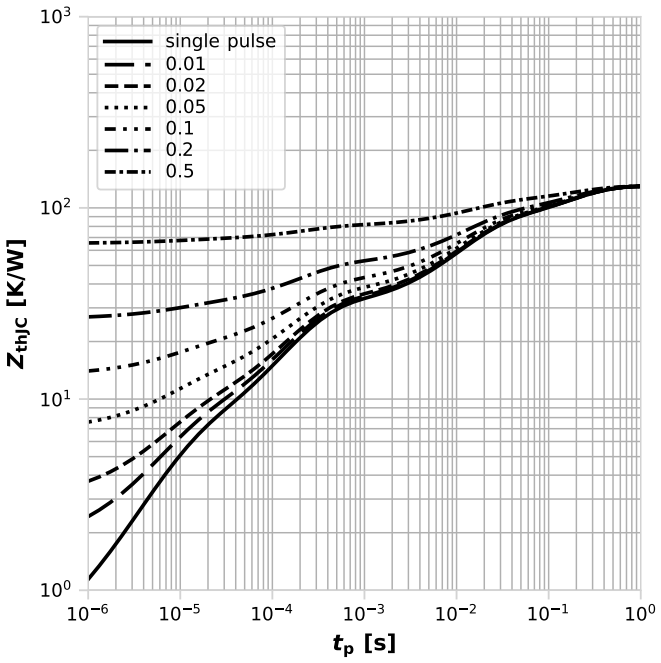
I_D=f(T_C); $|V_{GS}|$≥10 V

Diagram 3: Safe operating area



I_D=f(V_{DS}); T_C=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



Z_{thJC}=f(t_p); parameter: D=t_p/T

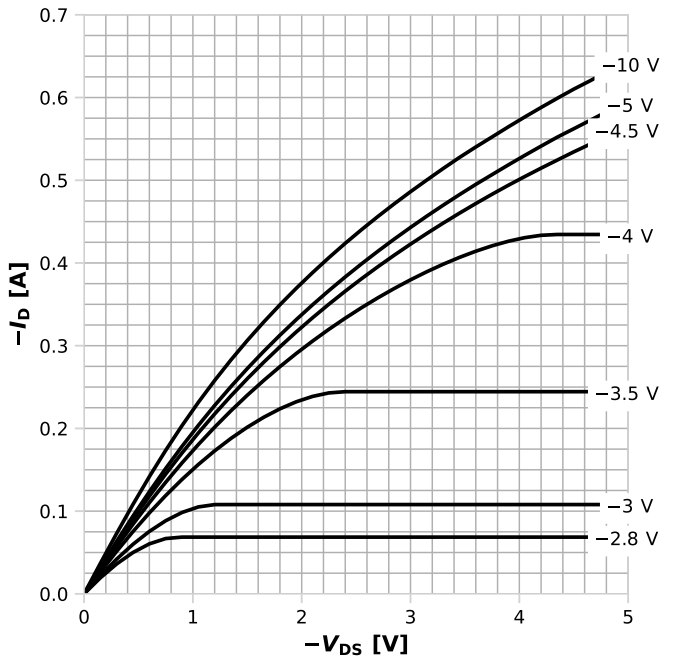
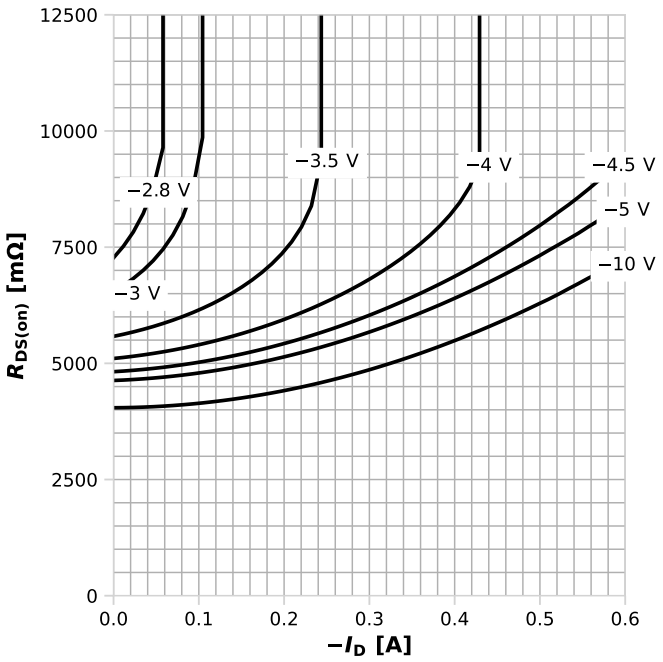
Diagram 5: Typ. output characteristics	Diagram 6: Typ. drain-source on resistance
	
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

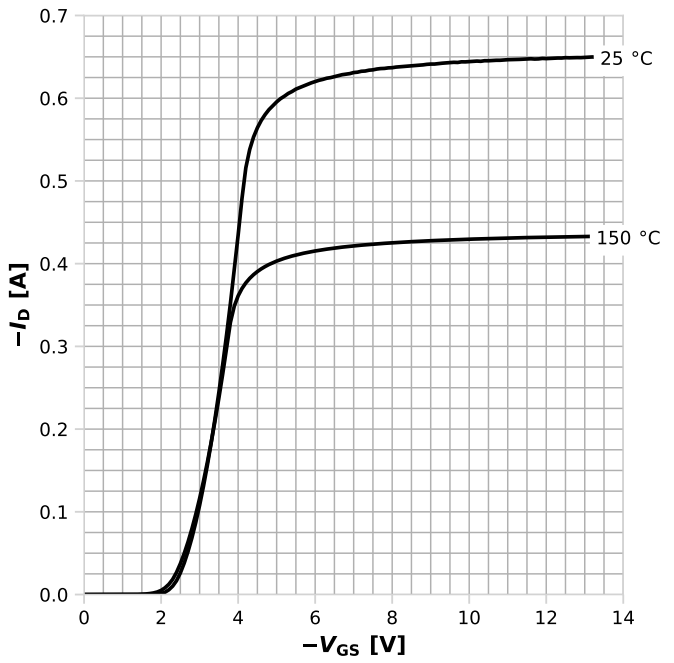
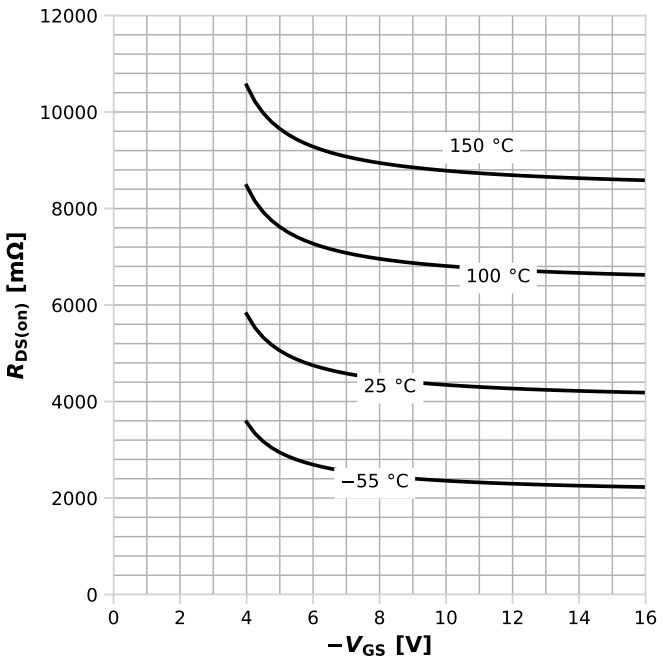
Diagram 7: Typ. transfer characteristics	Diagram 8: Typ. drain-source on resistance
	
I_D=f(V_{GS}), |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j	$R_{DS(on)}$=f(V_{GS}), I_D=-0.18 A; parameter: T_j

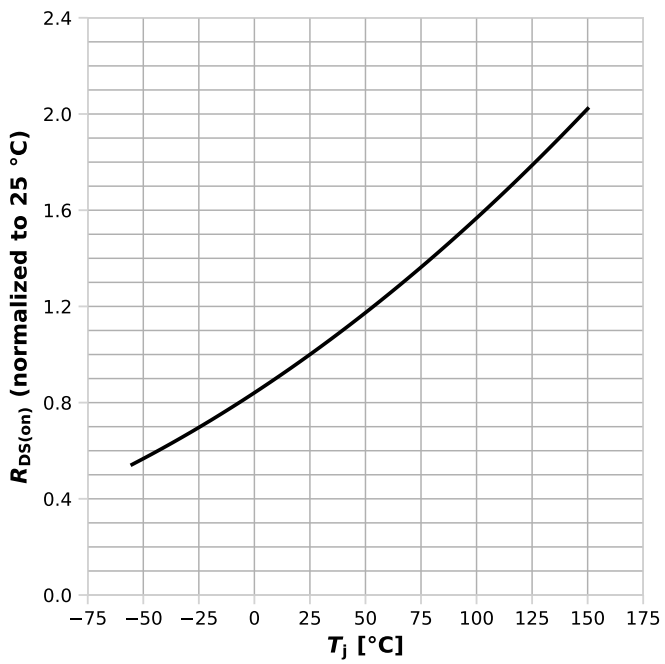
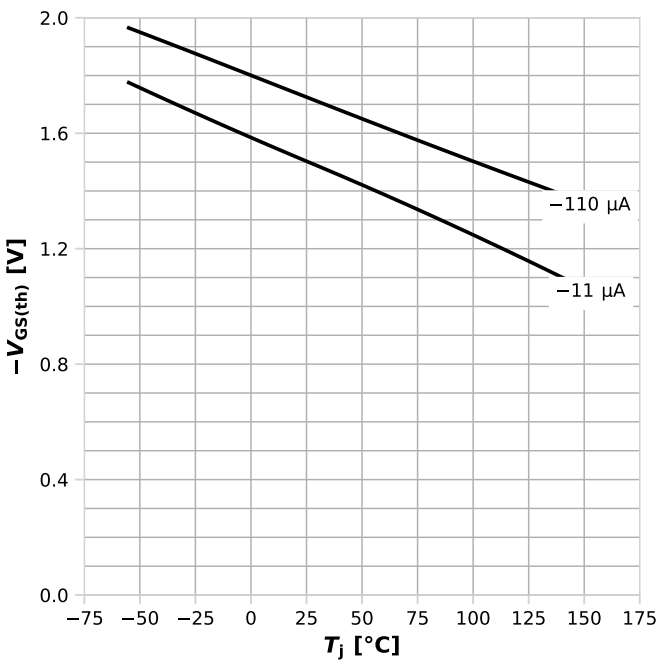
Diagram 9: Normalized drain-source on resistance	Diagram 10: Typ. gate threshold voltage
	
$R_{DS(on)}$=f(T_j), I_D=-0.18 A, V_{GS}=-10 V	$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

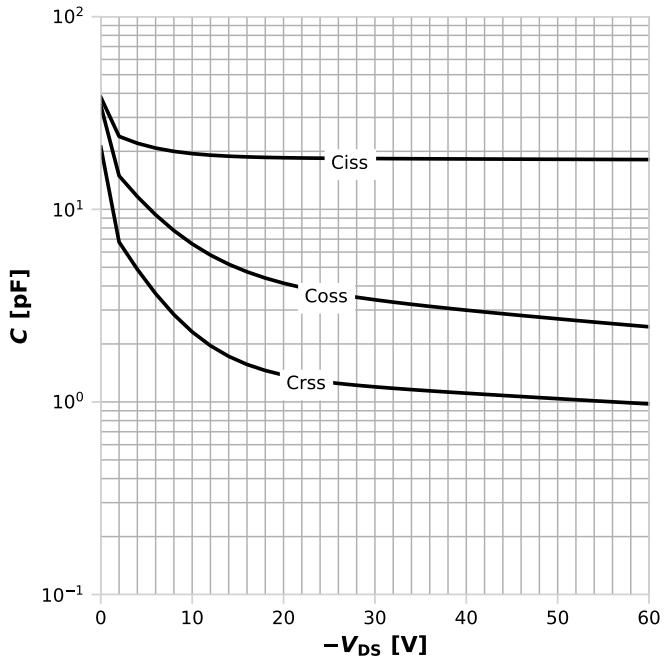
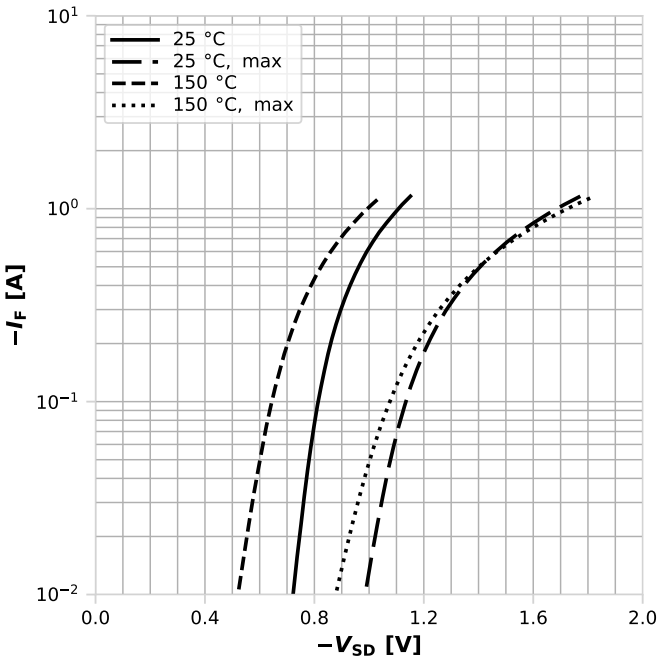
Diagram 11: Typ. capacitances	Diagram 12: Forward characteristics of reverse diode
	
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz	I_F=f(V_{SD}); parameter: T_j

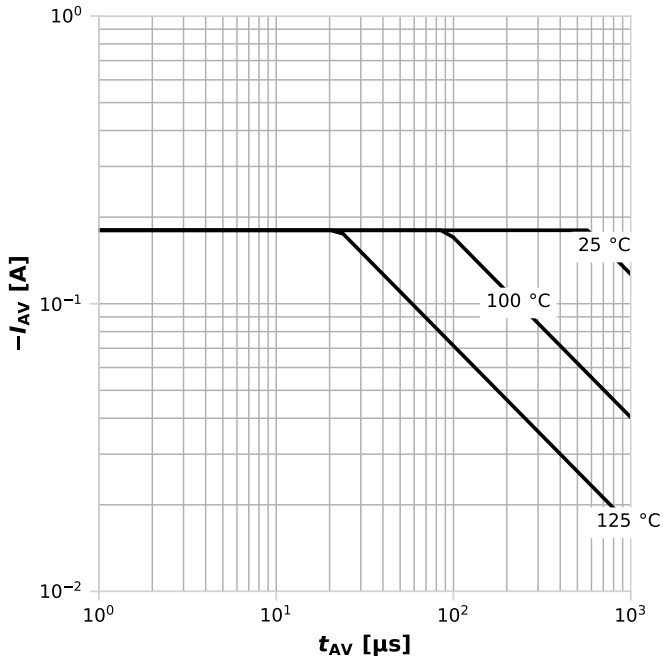
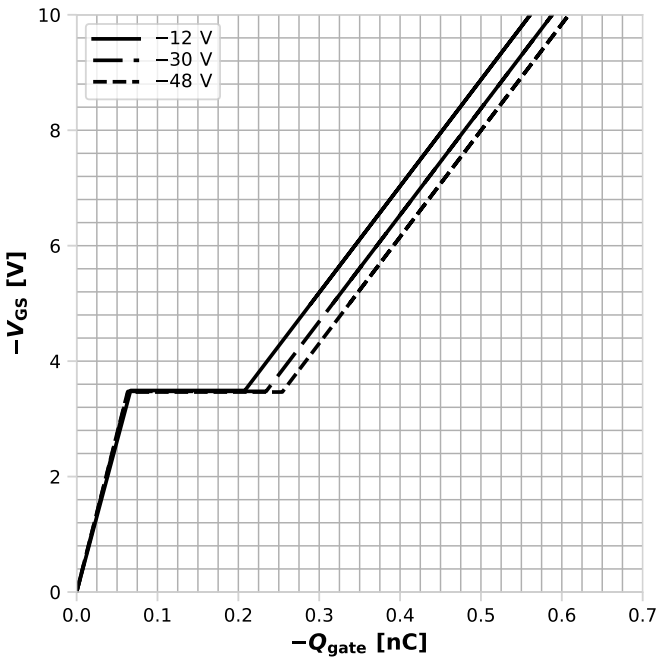
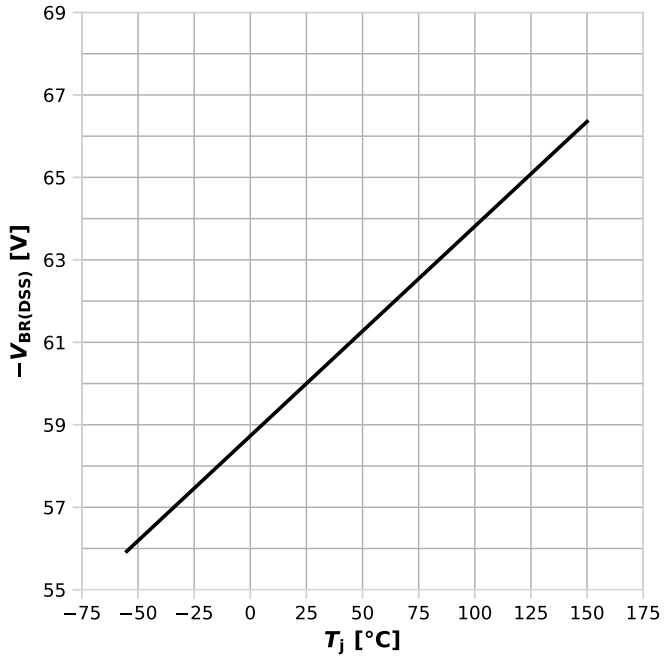
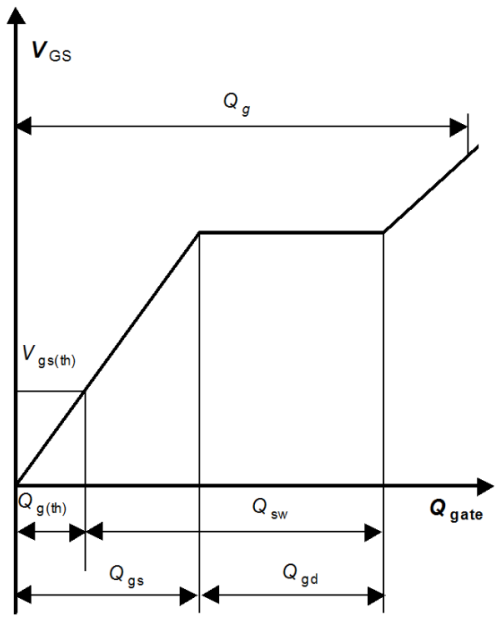
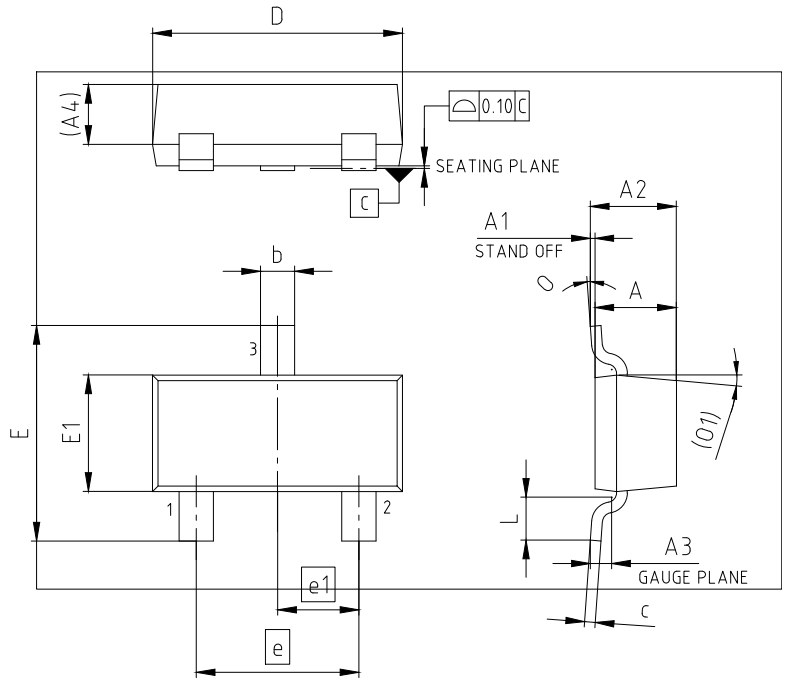
Diagram 13: Avalanche characteristics	Diagram 14: Typ. gate charge
	
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$	V_{GS}=f(Q_{gate}), I_D=-0.18 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage	Gate charge waveforms
	
$V_{BR(DSS)}$=f(T_j); I_D=-250 µA	-

5 Package outlines



PACKAGE - GROUP NUMBER:	PG-SOT23-3-U03				
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	0.88	1.02	e	1.90	
A1	0.01	0.10	e1	0.95	
A2	0.89	1.12	L	0.40	0.60
A3	0.15	0.35	N	3	
A4	0.70		O	3°	8°
b	0.32	0.47	O1	6°	8°
c	0.08	0.18			
D	2.80	3.04			
E	2.40	2.64			
E1	1.32	1.40			

NOTE: ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

Figure 1 Outline PG-SOT23-3mm

Revision history

BSS84I

Revision 2025-02-16, Rev. 2.0

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2025-02-16	Release of final datasheet

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